Space Charge Region and Poisson Equation

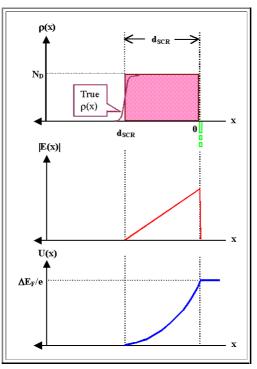
We start from a (constant) distribution of positive charges (for **n**-doped semiconductors) in the space charge region.

- The corresponding negative charges are all on the surface; the charge distribution is shown in the first frame of the illustration.
- <u>Poisson's equation</u> states that (for the one-dimensional case).

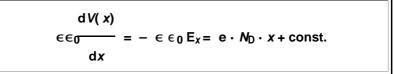
$$\epsilon \epsilon \frac{d^2 V(x)}{dx^2} = -\rho(x) = e \cdot N_D$$

For 0 < x < d_{SCR} and = 0 everywhere else. (We can also use the voltage U(x) instead of V(x) if we think as V(x = ∞) = 0). That will also be reflected in the choice of boundary conditions made below.

The drawing below shows the situation, including the slight approximation implicit in our choice of $\rho(x)$. Note that the *x*-direction ist to the left in this case.



The first straight-forward integration yields dU/d(x) which is the electrical field strength Ex = -dU/dx, or



With the boundary condition $E_x(x = d_{SCR}) = 0$, we obtain (always for the interval x = 0 and $x = d_{SCR}$, of course):

$$\mathbf{e} \cdot \mathbf{N}_{\mathrm{D}} \cdot \mathbf{d}_{\mathrm{SCR}} + \mathrm{const} = \mathbf{0}$$

const = $-\mathbf{e} \cdot \mathbf{N}_{\mathrm{D}} \cdot \mathbf{d}_{\mathrm{SCR}}$

$$E_{x} = \frac{1}{\underset{\epsilon \in 0}{\leftarrow}} \cdot (e \cdot N_{D}d_{SCR} - e \cdot N_{D} \cdot x)$$

The second integration yields

Illustration

$$\epsilon \epsilon_0 \cdot U(x) = \frac{\mathbf{e} \cdot N_{\mathrm{D}} \cdot x^2}{2} - \mathbf{e} \cdot N_{\mathrm{D}} \cdot d_{\mathrm{SCR}} \cdot x + \mathrm{const.}$$

With the boundary condition U(d_{SCR}) = 0, we obtain.

$$-\frac{e \cdot N_{\rm D} \cdot d^{2} {\rm SCR}}{2} + {\rm const.} = 0$$

$${\rm const.} = \frac{e \cdot N_{\rm D} \cdot d^{2} {\rm SCR}}{2}$$

Using the proper expression for the integration constant gives gives us the complete voltage function or the shape of the band bending

$$\epsilon \epsilon_0 \cdot U(x) = \frac{\mathbf{e} \cdot N_{\mathrm{D}} \cdot x^2}{2} - \mathbf{e} \cdot N_{\mathrm{D}} \cdot d_{\mathrm{SCR}} \cdot x + \frac{\mathbf{e} \cdot N_{\mathrm{D}} \cdot d^2_{\mathrm{SCR}}}{2}$$

The width of the space charge region can be obtained by considering the voltage at x = 0, where we have U(x = 0) = ΔE F/e.Using this we obtain

$$\frac{\epsilon \epsilon_0}{-} \cdot \Delta E_F = \frac{\mathbf{e} \cdot N_{\mathsf{D}} \cdot d^2 \mathrm{SCR}}{2}$$

This gives us the final result for the width of the space charge region

$$d_{\rm SCR} = \frac{1}{e} \cdot \left(\frac{2 \Delta E_{\rm F} \cdot \epsilon \epsilon_0}{N_{\rm D}}\right)^{1/2}$$

The corresponding curves are shown in the drawing above. We obtained the <u>same formula as before</u>, but now we have a better awareness of the approximations it contains.

The positive charge distribution was assumed to be box-shaped and uniform. This is a rather good approximation; the drawing indicates the precise shape of the charge distribution for comparison.

The counter charges are described by a δ -function at the surface; these charges only enter the calculation in the indirect form of a boundary condition.